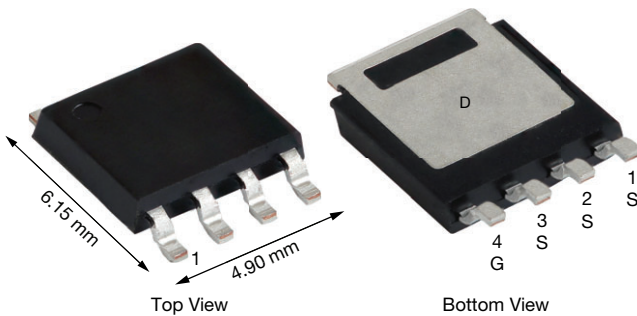
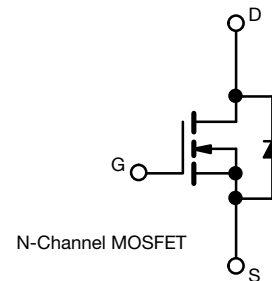


Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R_G and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE


RoHS
 COMPLIANT
 HALOGEN
FREE


PRODUCT SUMMARY	
V _{DS} (V)	40
R _{DS(on)} (Ω) at V _{GS} = 10 V	0.00124
I _D (A)	350
Configuration	Single
Package	PowerPAK SO-8L

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V _{DS}	40	V		
Gate-source voltage	V _{GS}	± 20			
Continuous drain current	I _D	T _C = 25 °C	350	A	
		T _C = 125 °C	234		
Continuous source current (diode conduction)	I _S	324	mJ		
Pulsed drain current ^a	I _{DM}	600			
Single pulse avalanche current	I _{AS}	48			
Single pulse avalanche energy	E _{AS}	115	W		
Maximum power dissipation ^a	P _D	T _C = 25 °C			500
		T _C = 125 °C	166		
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +175	°C		
Soldering recommendations (peak temperature) ^c		260			

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-ambient	R _{thJA}	68	°C/W	
Junction-to-case (drain)	R _{thJC}	0.3		

Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- When mounted on 1" square PCB (FR4 material)
- See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA	40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5	3.0	3.5	
Gate-source leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	-	-	1	μA
		V _{GS} = 0 V, V _{DS} = 40 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V, V _{DS} = 40 V, T _J = 175 °C	-	-	250	
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V, V _{DS} ≥ 5 V	30	-	-	A
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A	-	0.00103	0.00124	Ω
		V _{GS} = 10 V, I _D = 15 A, T _J = 125 °C	-	-	0.00190	
		V _{GS} = 10 V, I _D = 15 A, T _J = 175 °C	-	-	0.00223	
Forward transconductance ^b	g _{fs}	V _{DS} = 15 V, I _D = 10 A	-	95	-	S
Dynamic ^b						
Input capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz	-	5309	6636	pF
Output capacitance	C _{oss}		-	1521	1902	
Reverse transfer capacitance	C _{rss}		-	138	175	
Total gate charge ^c	Q _g	V _{GS} = 10 V, V _{DS} = 20 V, I _D = 40 A	-	86	107	nC
Gate-source charge ^c	Q _{gs}		-	23.6	-	
Gate-drain charge ^c	Q _{gd}		-	6	-	
Gate resistance	R _g	f = 1 MHz	1	1.65	2.64	Ω
Turn-on delay time ^c	t _{d(on)}	V _{DD} = 20 V, R _L = 0.5 Ω I _D ≅ 40 A, V _{GEN} = 10 V, R _g = 1 Ω	-	18	24	ns
Rise time ^c	t _r		-	17	21	
Turn-off delay time ^c	t _{d(off)}		-	35	44	
Fall time ^c	t _f		-	13	17	
Source-Drain Diode Ratings and Characteristics ^b						
Pulsed current ^a	I _{SM}		-	-	600	A
Forward voltage	V _{SD}	I _F = 15 A, V _{GS} = 0 V	-	-	1.1	V
Body diode reverse recovery time	t _{rr}	I _F = 40 A, di/dt = 100 A/μs	-	52	68	ns
Body diode reverse recovery charge	Q _{rr}		-	36	47	nC
Reverse recovery fall time	t _a		-	27	46	ns
Reverse recovery rise time	t _b		-	25	46	
Body diode peak reverse recovery current	I _{RM(REC)}			-	1.3	2.2

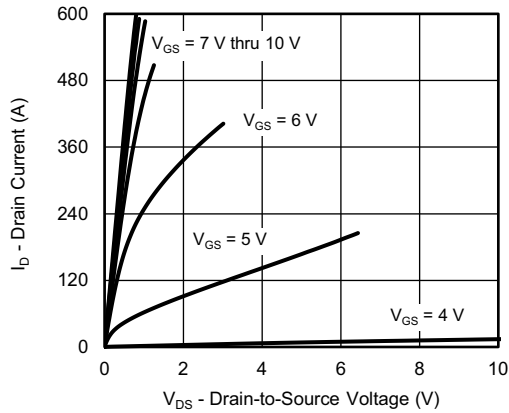
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
b. Guaranteed by design, not subject to production testing
c. Independent of operating temperature

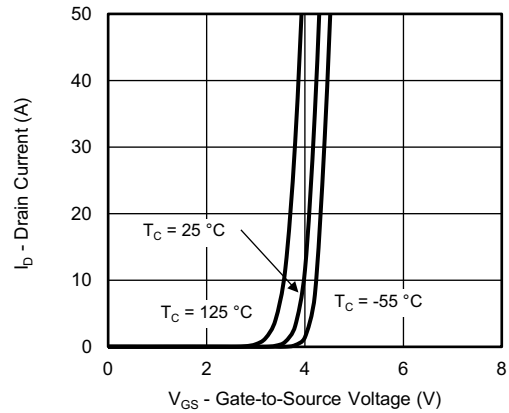
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



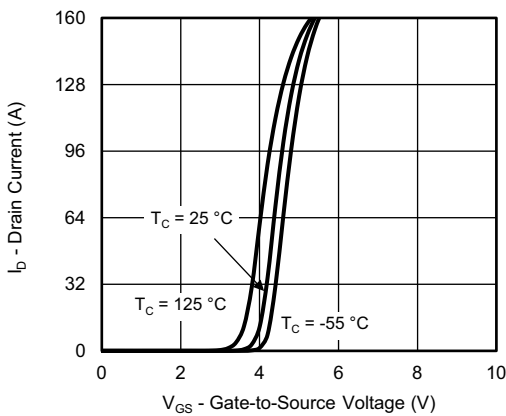
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



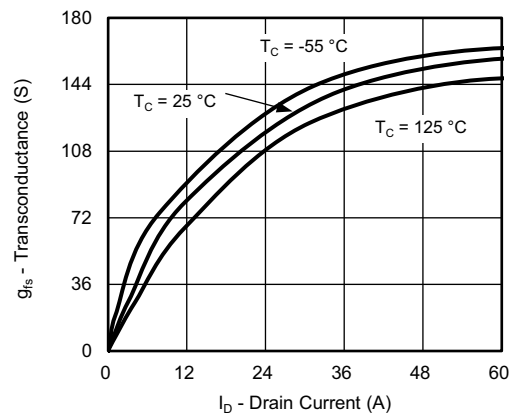
Output Characteristics



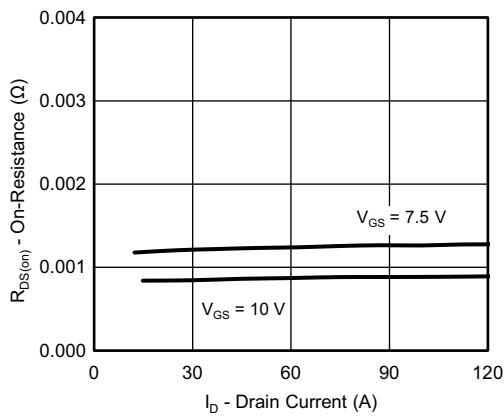
Transfer Characteristics



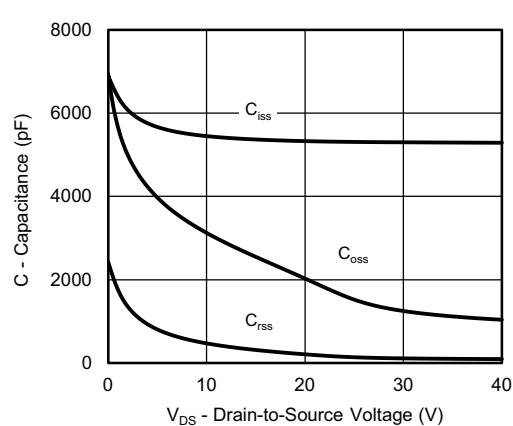
Transfer Characteristics



Transconductance



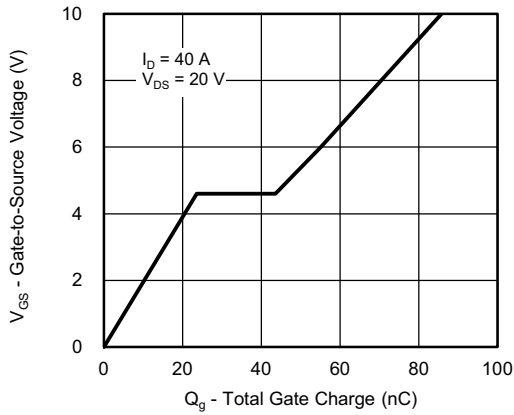
On-Resistance vs. Drain Current



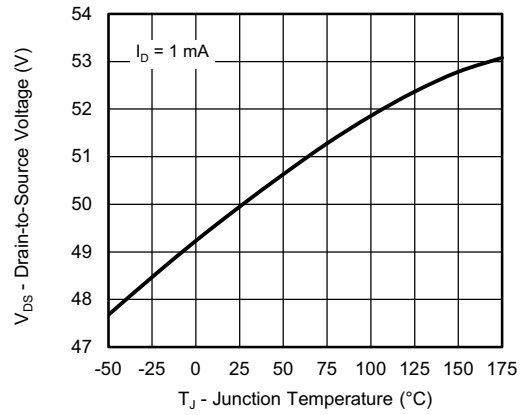
Capacitance



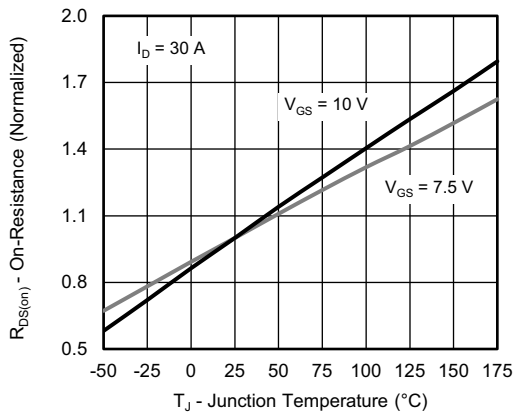
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



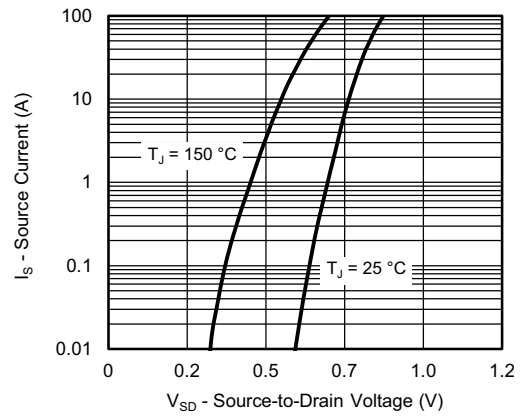
Gate Charge



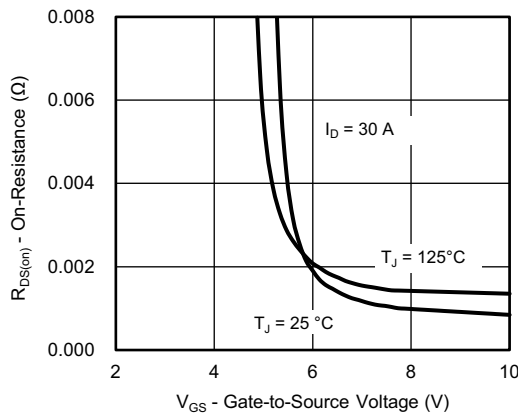
Drain Source Breakdown vs. Junction Temperature



On-Resistance vs. Junction Temperature



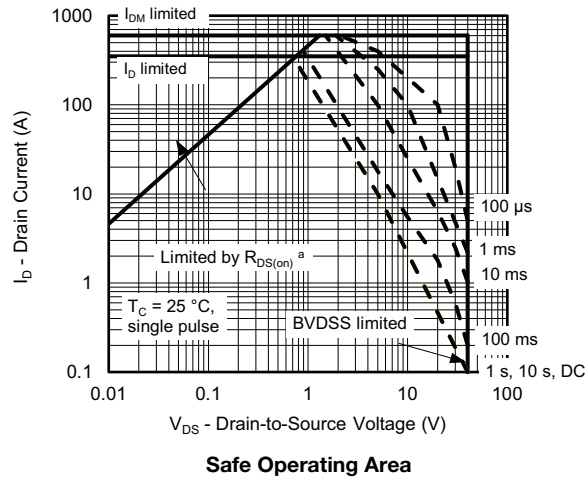
Source Drain Diode Forward Voltage



On-Resistance vs. Gate to Source Voltage



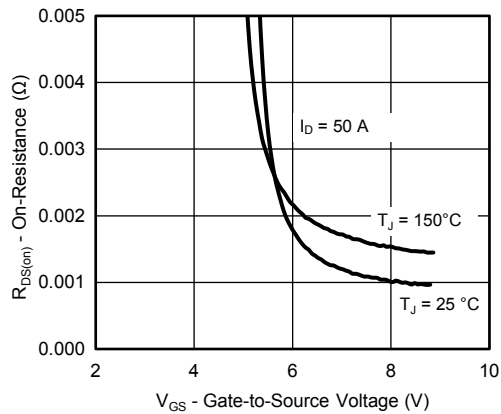
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



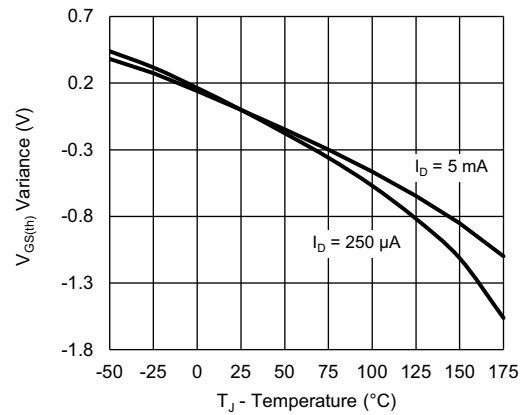
Safe Operating Area

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



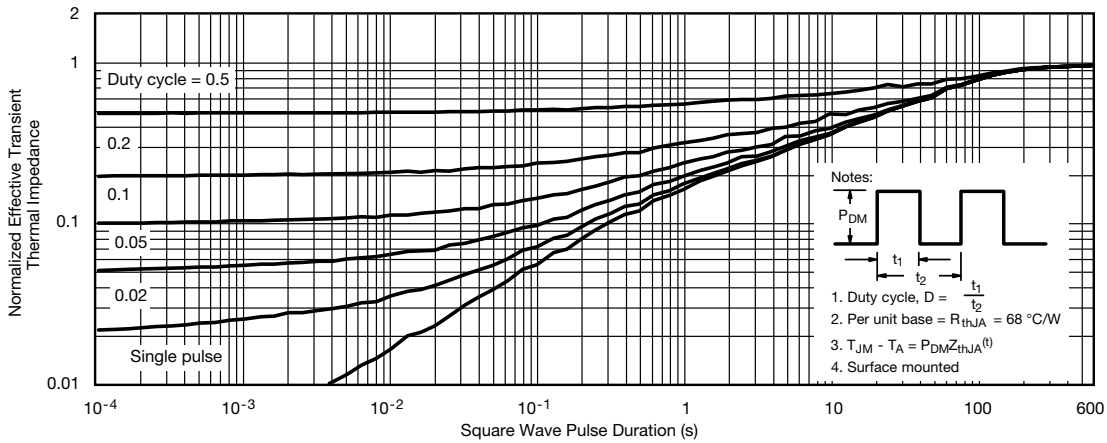
On-Resistance vs. Gate-to Source Voltage



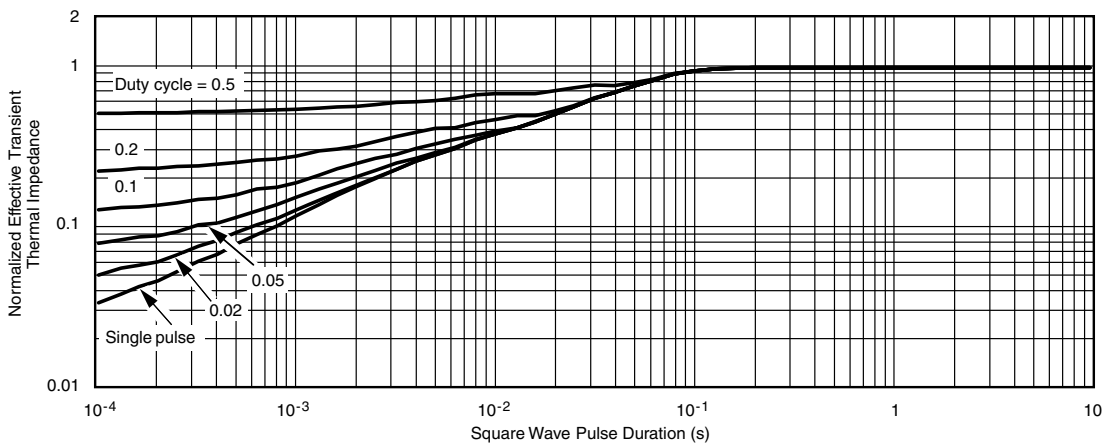
Threshold Voltage



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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